NEC

MOS INTEGRATED CIRCUIT

μPD42S17800,4217800

16 M-BIT DYNAMIC RAM
2 M-WORD BY 8-BIT, FAST PAGE MODE

★ Description

The μPD42S17800, 4217800 are 2,097,152 words by 8 bits CMOS dynamic RAMs. The fast page mode capability realize high speed access and low power consumption.

Besides, the μPD42S17800 can execute $\overline{CAS}$ before $\overline{RAS}$ self refresh.

These are packaged in 28-pin plastic TSOP(II) and 28-pin plastic SOJ.

★ Features

- 2,097,152 words by 8 bits organization
- Fast page mode
- Fast access and cycle time
- Single +5.0 V ± 10 % power supply

Part number	Power consumption (MAX.)		Access time (MAX.)	R/W cycle time (MIN.)	Fast page mode cycle time (MIN.)
	Active	Standby			
μPD42S17800-50, 4217800-50	660 mW	1.4 mW (CMOS level input)	50 ns	90 ns	35 ns
μPD42S17800-60, 4217800-60	605 mW		60 ns	110 ns	40 ns
μPD42S17800-70, 4217800-70	550 mW	5.5 mW (CMOS level input)	70 ns	130 ns	45 ns
μPD42S17800-80, 4217800-80	495 mW		80 ns	150 ns	50 ns

- The μPD42S17800 can execute $\overline{CAS}$ before $\overline{RAS}$ self refresh

Part number	Refresh cycle	Refresh
μPD42S17800	2,048 cycles/128 ms	$\overline{CAS}$ before $\overline{RAS}$ self refresh, $\overline{CAS}$ before $\overline{RAS}$ refresh, $\overline{RAS}$ only refresh, Hidden refresh
μPD4217800	2,048 cycles/32 ms	$\overline{CAS}$ before $\overline{RAS}$ refresh, $\overline{RAS}$ only refresh, Hidden refresh

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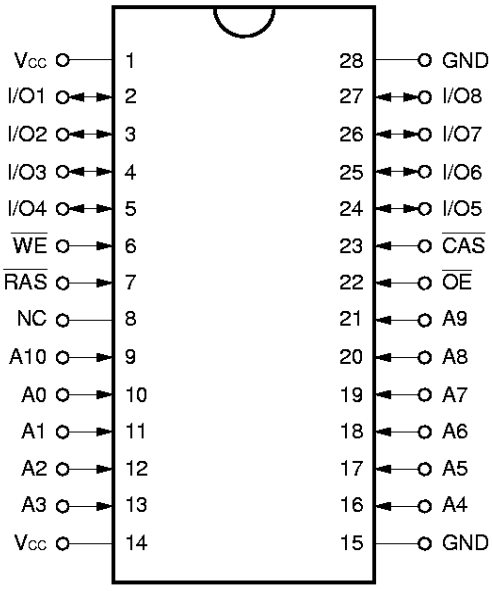
The mark ★ shows major revised points.

★ Ordering Information

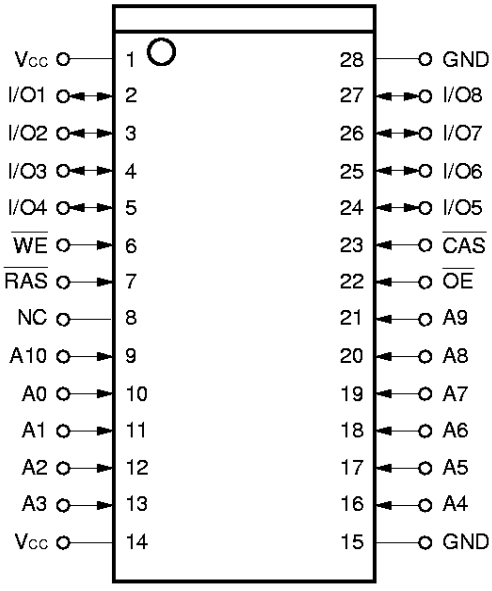
Part number	Access time (MAX.)	Package	Refresh
μPD42S17800G5-50-7JD	50 ns	28-pin plastic TSOP (II) (400 mil)	$\overline{CAS}$ before $\overline{RAS}$ self refresh $\overline{CAS}$ before $\overline{RAS}$ refresh $\overline{RAS}$ only refresh Hidden refresh
μPD42S17800G5-60-7JD	60 ns		
μPD42S17800G5-70-7JD	70 ns		
μPD42S17800G5-80-7JD	80 ns		
μPD42S17800LE-50	50 ns	28-pin plastic SOJ (400 mil)	
μPD42S17800LE-60	60 ns		
μPD42S17800LE-70	70 ns		
μPD42S17800LE-80	80 ns		
μPD4217800G5-50-7JD	50 ns	28-pin plastic TSOP (II) (400 mil)	$\overline{CAS}$ before $\overline{RAS}$ refresh $\overline{RAS}$ only refresh Hidden refresh
μPD4217800G5-60-7JD	60 ns		
μPD4217800G5-70-7JD	70 ns		
μPD4217800G5-80-7JD	80 ns		
μPD4217800LE-50	50 ns	28-pin plastic SOJ (400 mil)	
μPD4217800LE-60	60 ns		
μPD4217800LE-70	70 ns		
μPD4217800LE-80	80 ns		

★ **Pin Configurations** (Marking Side)

28-pin Plastic TSOP (II) (400 mil)
μPD42S17800G5-7JD
μPD4217800G5-7JD

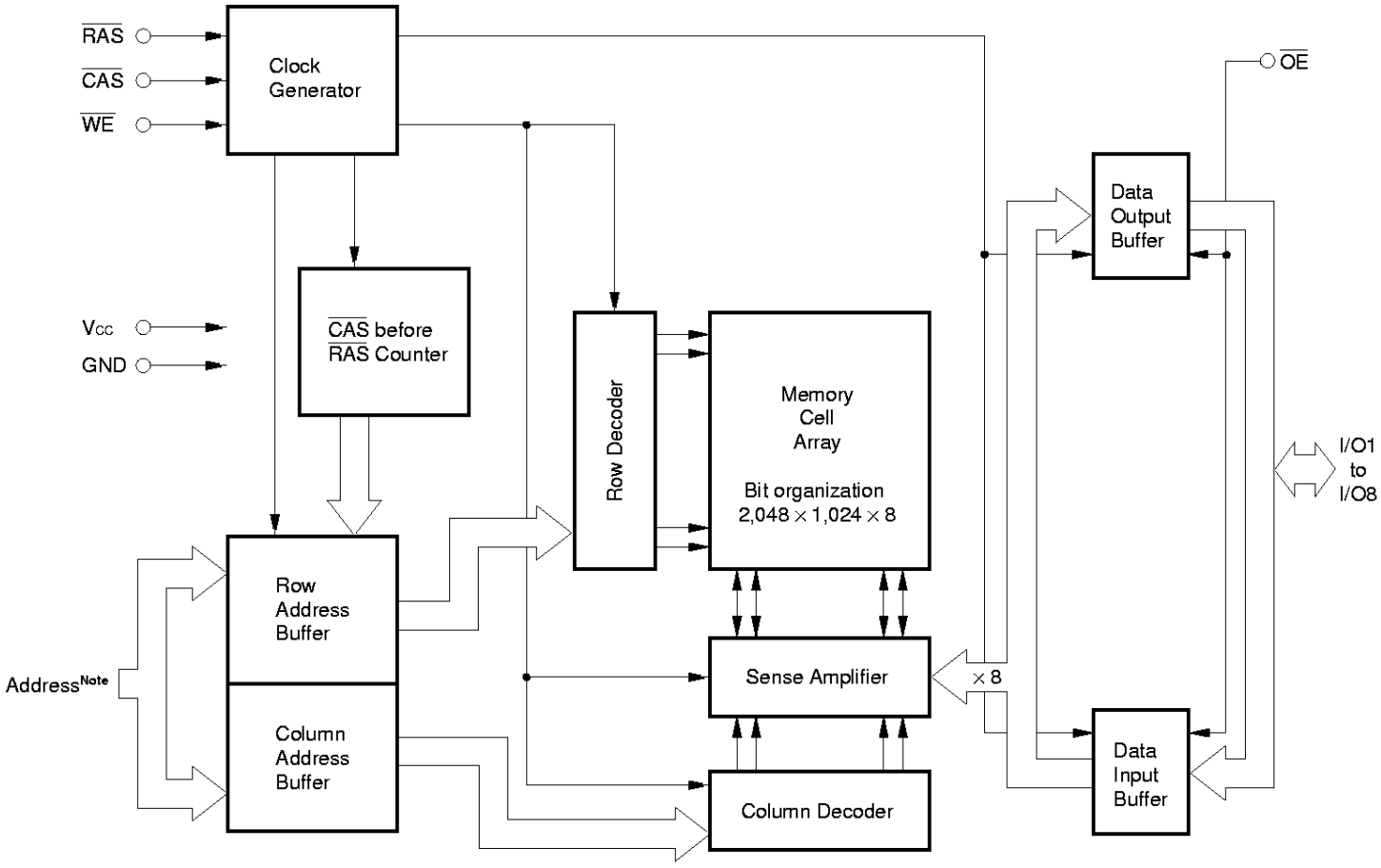


28-pin Plastic SOJ (400 mil)
μPD42S17800LE
μPD4217800LE



A0 to A10	:	Address inputs
I/O1 to I/O8	:	Data Inputs/Outputs
$\overline{RAS}$	:	Row address strobe
$\overline{CAS}$	:	Column address strobe
$\overline{WE}$	:	Write enable
$\overline{OE}$	:	Output enable
VCC	:	Power Supply
GND	:	Ground
NC	:	No connection

Block Diagram



Note

Part number	Row address	Column address
μPD42S17800, 4217800	A0 – A10	A0 – A9

Input/Output Pin Functions

The μPD42S17800, 4217800 have input pins $\overline{RAS}$, $\overline{CAS}$, $\overline{WE}$, $\overline{OE}$, A0-A10 and input/output pins I/O1 to I/O8.

Pin name	Input/Output	Function
$\overline{RAS}$ (Row address strobe)	Input	$\overline{RAS}$ activates the sense amplifier by latching a row address and selecting a corresponding word line. It refreshes memory cell array of one line selected by the row address. It also selects the following function. • $\overline{CAS}$ before $\overline{RAS}$ refresh
$\overline{CAS}$ (Column address strobe)	Input	$\overline{CAS}$ activates data input/output circuit by latching column address and selecting a digit line connected with the sense amplifier.
A0 to A10 (Address inputs)	Input	Address bus. Input total 21-bit of address signal, upper 11-bit and lower 10-bit in sequence (address multiplex method). Therefore, one word is selected from 2,097,152-word by 8-bit memory cell array. In actual operation, latch row address by specifying row address and activating $\overline{RAS}$. Then, switch the address bus to column address and activate $\overline{CAS}$. Each address is taken into the device when $\overline{RAS}$ and $\overline{CAS}$ are activated. Therefore, the address input setup time (t_{ASR}, t_{ASC}) and hold time (t_{RAH}, t_{CAH}) are specified for the activation of $\overline{RAS}$ and $\overline{CAS}$.
$\overline{WE}$ (Write enable)	Input	Write control signal. Write operation is executed by activating $\overline{RAS}$, $\overline{CAS}$ and $\overline{WE}$.
$\overline{OE}$ (Output enable)	Input	Read control signal. Read operation can be executed by activating $\overline{RAS}$, $\overline{CAS}$ and $\overline{OE}$. If $\overline{WE}$ is activated during read operation, $\overline{OE}$ is to be ineffective in the device. Therefore, read operation cannot be executed.
I/O1 to I/O8 (Data inputs/outputs)	Input/Output	8-bit data bus. I/O1 to I/O8 are used to input/output data.

Electrical Specifications

- All voltages are referenced to GND.
- After power up ($V_{CC} \geq V_{CC\,(MIN.)}$), wait more than 100 μs ($\overline{RAS}$, $\overline{CAS}$ inactive) and then, execute eight $\overline{CAS}$ before $\overline{RAS}$ or $\overline{RAS}$ only refresh cycles as dummy cycles to initialize internal circuit.

Absolute Maximum Ratings

Parameter	Symbol	Condition	Rating	Unit
Voltage on any pin relative to GND	V_T		–1.0 to +7.0	V
Supply voltage	V_{CC}		–1.0 to +7.0	V
Output current	I_O		50	mA
Power dissipation	P_D		1	W
Operating ambient temperature	T_A		0 to +70	°C
Storage temperature	T_{stg}		–55 to +125	°C

Caution Exposing the device to stress above those listed in Absolute Maximum Ratings could cause permanent damage. The device is not meant to be operated under conditions outside the limits described in the operational section of this specification. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability.

Recommended Operating Conditions

Parameter	Symbol	Condition	MIN.	TYP.	MAX.	Unit
Supply voltage	V_{CC}		4.5	5.0	5.5	V
High level input voltage	V_{IH}		2.4		V_{CC} + 1.0	V
Low level input voltage	V_{IL}		–1.0		+0.8	V
Operating ambient temperature	T_A		0		70	°C

Capacitance (T_A = 25 °C, f = 1 MHz)

Parameter	Symbol	Test condition	MIN.	TYP.	MAX.	Unit
Input capacitance	C_{I1}	Address			5	pF
	C_{I2}	$\overline{RAS}$, $\overline{CAS}$, $\overline{WE}$, $\overline{OE}$			7	
Data input/output capacitance	$C_{I/O}$	I/O			7	pF

DC Characteristics (Recommended operating conditions unless otherwise noted)

Parameter		Symbol	Test condition		MIN.	MAX.	Unit	Notes
Operating current		I_{CC1}	$\overline{RAS}$, $\overline{CAS}$ cycling $t_{RC} = t_{RC\ (MIN.)}$ I_O = 0 mA	t_{RAC} = 50 ns		120	mA	1, 2, 3
				t_{RAC} = 60 ns		110		
				t_{RAC} = 70 ns		100		
				t_{RAC} = 80 ns		90		
Standby current	μPD42S17800	I_{CC2}	$\overline{RAS}$, $\overline{CAS} \geq V_{IH\ (MIN.)}$, I_O = 0 mA			2.0	mA	
			$\overline{RAS}$, $\overline{CAS} \geq V_{CC}$ – 0.2 V, I_O = 0 mA			0.25		
	μPD4217800		$\overline{RAS}$, $\overline{CAS} \geq V_{IH\ (MIN.)}$, I_O = 0 mA			2.0		
			$\overline{RAS}$, $\overline{CAS} \geq V_{CC}$ – 0.2 V, I_O = 0 mA			1.0		
$\overline{RAS}$ only refresh current		I_{CC3}	$\overline{RAS}$ cycling, $\overline{CAS} \geq V_{IH\ (MIN.)}$ $t_{RC} = t_{RC\ (MIN.)}$, I_O = 0 mA	t_{RAC} = 50 ns		120	mA	1, 2, 3 ,4
				t_{RAC} = 60 ns		110		
				t_{RAC} = 70 ns		100		
				t_{RAC} = 80 ns		90		
Operating current (Fast page mode)		I_{CC4}	$\overline{RAS} \leq V_{IL\ (MAX.)}$, $\overline{CAS}$ cycling $t_{PC} = t_{PC\ (MIN.)}$, I_O = 0 mA	t_{RAC} = 50 ns		80	mA	1, 2, 5
				t_{RAC} = 60 ns		70		
				t_{RAC} = 70 ns		60		
				t_{RAC} = 80 ns		50		
$\overline{CAS}$ before $\overline{RAS}$ refresh current		I_{CC5}	$\overline{RAS}$ cycling $t_{RC} = t_{RC\ (MIN.)}$ I_O = 0 mA	t_{RAC} = 50 ns		120	mA	1, 2
				t_{RAC} = 60 ns		110		
				t_{RAC} = 70 ns		100		
				t_{RAC} = 80 ns		90		
$\overline{CAS}$ before $\overline{RAS}$ long refresh current (2,048 cycles / 128 ms, only for the μPD42S17800)		I_{CC6}	$\overline{CAS}$ before $\overline{RAS}$ refresh : t_{RC} = 62.5 μs $\overline{RAS}$, $\overline{CAS}$: V_{CC} – 0.2 V ≤ $V_{IH} \leq V_{IH\ (MAX.)}$ 0 V ≤ V_{IL} ≤ 0.2 V	$t_{RAS} \leq$ 300 ns		400	μA	1, 2
			Standby : $\overline{RAS}$, $\overline{CAS} \geq V_{CC}$ – 0.2 V Address : V_{IH} or V_{IL} $\overline{WE}$, $\overline{OE}$: V_{IH} I_O = 0 mA	$t_{RAS} \leq$ 1 μs		500	μA	1, 2
$\overline{CAS}$ before $\overline{RAS}$ self refresh current (only for the μPD42S17800)		I_{CC7}	$\overline{RAS}$, $\overline{CAS}$: t_{RASS} = 5 ms V_{CC} – 0.2 V ≤ $V_{IH} \leq V_{IH(MAX.)}$ 0 V ≤ V_{IL} ≤ 0.2 V I_O = 0 mA			250	μA	2
Input leakage current		$I_{I\ (L)}$	V_I = 0 to 5.5 V All other pins not under test = 0 V		–10	+10	μA	
Output leakage current		$I_{O\ (L)}$	V_O = 0 to 5.5 V Output is disabled (Hi-Z)		–10	+10	μA	
High level output voltage		V_{OH}	I_O = –5.0 mA		2.4		V	
Low level output voltage		V_{OL}	I_O = +4.2 mA			0.4	V	

Notes 1. I_{CC1}, I_{CC3}, I_{CC4}, I_{CC5} and I_{CC6} depend on cycle rates (t_{RC} and t_{PC}).

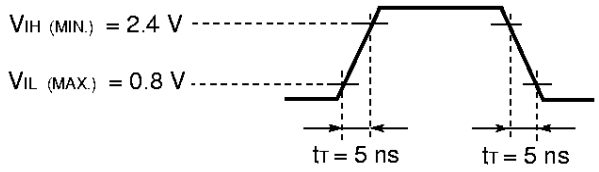
2. Specified values are obtained with outputs unloaded.

3. I_{CC1} and I_{CC3} are measured assuming that address can be changed once or less during $\overline{RAS} \leq V_{IL\ (MAX.)}$ and $\overline{CAS} \geq V_{IH\ (MIN.)}$.
4. I_{CC3} is measured assuming that all column address inputs are held at either high or low.
5. I_{CC4} is measured assuming that all column address inputs are switched only once during each fast page cycle.

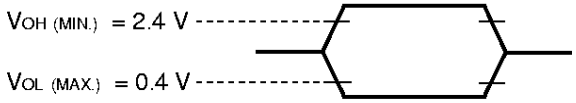
AC Characteristics (Recommended Operating Conditions unless otherwise noted)

AC Characteristics Test Conditions

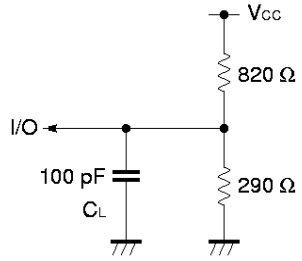
(1) Input timing specification



(2) Output timing specification



(3) Output load condition



Common to Read, Write, Read Modify Write Cycle

Parameter		Symbol	tRAC = 50 ns		tRAC = 60 ns		tRAC = 70 ns		tRAC = 80 ns		Unit	Notes
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Read / Write cycle time		tRC	90	–	110	–	130	–	150	–	ns	
$\overline{RAS}$ precharge time		tRP	30	–	40	–	50	–	60	–	ns	
$\overline{CAS}$ precharge time		tCPN	8	–	10	–	10	–	10	–	ns	
$\overline{RAS}$ pulse width		tRAS	50	10,000	60	10,000	70	10,000	80	10,000	ns	1
$\overline{CAS}$ pulse width		tCAS	13	10,000	15	10,000	18	10,000	20	10,000	ns	
$\overline{RAS}$ hold time		tRSH	13	–	15	–	18	–	20	–	ns	
$\overline{CAS}$ hold time		tCSH	50	–	60	–	70	–	80	–	ns	
$\overline{RAS}$ to $\overline{CAS}$ delay time		tRCD	18	37	20	45	20	52	25	60	ns	2
$\overline{RAS}$ to column address delay time		tRAD	13	25	15	30	15	35	17	40	ns	2
$\overline{CAS}$ to $\overline{RAS}$ precharge time		tCRP	5	–	5	–	5	–	5	–	ns	3
Row address setup time		tASR	0	–	0	–	0	–	0	–	ns	
Row address hold time		tRAH	8	–	10	–	10	–	12	–	ns	
Column address setup time		tASC	0	–	0	–	0	–	0	–	ns	
Column address hold time		tCAH	13	–	15	–	15	–	15	–	ns	
$\overline{OE}$ lead time referenced to $\overline{RAS}$		tOES	0	–	0	–	0	–	0	–	ns	
$\overline{CAS}$ to data setup time		tCLZ	0	–	0	–	0	–	0	–	ns	
$\overline{OE}$ to data setup time		tOLZ	0	–	0	–	0	–	0	–	ns	
$\overline{OE}$ to data delay time		tOED	10	–	13	–	15	–	15	–	ns	
Transition time (rise and fall)		tT	3	50	3	50	3	50	3	50	ns	
Refresh time	μPD42S17800	tREF	–	128	–	128	–	128	–	128	ms	4
	μPD4217800		–	32	–	32	–	32	–	32	ms	

Notes 1. In $\overline{CAS}$ before $\overline{RAS}$ refresh cycles, $t_{RAS\ (MAX.)}$ is 100 μs.
If 10 μs < t_{RAS} < 100 μs, $\overline{RAS}$ precharge time for $\overline{CAS}$ before $\overline{RAS}$ self refresh (t_{RPS}) is applied.

2. For read cycles, access time is defined as follows:

Input conditions	Access time	Access time from $\overline{RAS}$
$t_{RAD} \leq t_{RAD\ (MAX.)}$ and $t_{RCD} \leq t_{RCD\ (MAX.)}$	$t_{RAC\ (MAX.)}$	$t_{RAC\ (MAX.)}$
$t_{RAD} > t_{RAD\ (MAX.)}$ and $t_{RCD} \leq t_{RCD\ (MAX.)}$	$t_{AA\ (MAX.)}$	$t_{RAD} + t_{AA\ (MAX.)}$
$t_{RCD} > t_{RCD\ (MAX.)}$	$t_{CAC\ (MAX.)}$	$t_{RCD} + t_{CAC\ (MAX.)}$

$t_{RAD\ (MAX.)}$ and $t_{RCD\ (MAX.)}$ are specified as reference points only ; they are not restrictive operating parameters. They are used to determine which access time (t_{RAC}, t_{AA} or t_{CAC}) is to be used for finding out when output data will be available. Therefore, the input conditions $t_{RAD} \geq t_{RAD\ (MAX.)}$ and $t_{RCD} \geq t_{RCD\ (MAX.)}$ will not cause any operation problems.

3. $t_{CRP\ (MIN.)}$ requirement is applied to $\overline{RAS}$, $\overline{CAS}$ cycles.

4. This specification is applied only to the μPD42S17800.

Read Cycle

Parameter	Symbol	t_{RAC} = 50 ns		t_{RAC} = 60 ns		t_{RAC} = 70 ns		t_{RAC} = 80 ns		Unit	Notes
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Access time from $\overline{RAS}$	t_{RAC}	–	50	–	60	–	70	–	80	ns	1
Access time from $\overline{CAS}$	t_{CAC}	–	13	–	15	–	18	–	20	ns	1
Access time from column address	t_{AA}	–	25	–	30	–	35	–	40	ns	1
Access time from $\overline{OE}$	t_{OEA}	–	13	–	15	–	18	–	20	ns	
Column address lead time referenced to $\overline{RAS}$	t_{RAL}	25	–	30	–	35	–	40	–	ns	
Read command setup time	t_{RCS}	0	–	0	–	0	–	0	–	ns	
Read command hold time referenced to $\overline{RAS}$	t_{RRH}	0	–	0	–	0	–	0	–	ns	2
Read command hold time referenced to $\overline{CAS}$	t_{RCH}	0	–	0	–	0	–	0	–	ns	2
Output buffer turn-off delay time from $\overline{OE}$	t_{OEZ}	0	10	0	13	0	15	0	15	ns	3
Output buffer turn-off delay time from $\overline{CAS}$	t_{OFF}	0	10	0	13	0	15	0	15	ns	3

Notes 1. For read cycles, access time is defined as follows:

Input conditions	Access time	Access time from $\overline{RAS}$
$t_{RAD} \leq t_{RAD\ (MAX.)}$ and $t_{RCD} \leq t_{RCD\ (MAX.)}$	$t_{RAC\ (MAX.)}$	$t_{RAC\ (MAX.)}$
$t_{RAD} > t_{RAD\ (MAX.)}$ and $t_{RCD} \leq t_{RCD\ (MAX.)}$	$t_{AA\ (MAX.)}$	$t_{RAD} + t_{AA\ (MAX.)}$
$t_{RCD} > t_{RCD\ (MAX.)}$	$t_{CAC\ (MAX.)}$	$t_{RCD} + t_{CAC\ (MAX.)}$

$t_{RAD\ (MAX.)}$ and $t_{RCD\ (MAX.)}$ are specified as reference points only; they are not restrictive operating parameters. They are used to determine which access time (t_{RAC}, t_{AA} or t_{CAC}) is to be used for finding out when output data will be available. Therefore, the input conditions $t_{RAD} \geq t_{RAD\ (MAX.)}$ and $t_{RCD} \geq t_{RCD\ (MAX.)}$ will not cause any operation problems.

2. Either $t_{RCH\ (MIN.)}$ or $t_{RRH\ (MIN.)}$ should be met in read cycles.

3. $t_{OFF\ (MAX.)}$ and $t_{OEZ\ (MAX.)}$ define the time when the output achieves the condition of Hi-Z and is not referenced to V_{OH} or V_{OL}.

Write Cycle

Parameter	Symbol	t_{RAC} = 50 ns		t_{RAC} = 60 ns		t_{RAC} = 70 ns		t_{RAC} = 80 ns		Unit	Notes
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
$\overline{WE}$ hold time referenced to $\overline{CAS}$	t_{WCH}	8	–	10	–	10	–	15	–	ns	1
$\overline{WE}$ pulse width	t_{WP}	8	–	10	–	10	–	15	–	ns	1
$\overline{WE}$ lead time referenced to $\overline{RAS}$	t_{RWL}	18	–	20	–	20	–	20	–	ns	
$\overline{WE}$ lead time referenced to $\overline{CAS}$	t_{CWL}	13	–	15	–	15	–	15	–	ns	
$\overline{WE}$ setup time	t_{WCS}	0	–	0	–	0	–	0	–	ns	2
$\overline{OE}$ hold time	t_{OEH}	0	–	0	–	0	–	0	–	ns	
Data-in setup time	t_{DS}	0	–	0	–	0	–	0	–	ns	3
Data-in hold time	t_{DH}	10	–	10	–	15	–	15	–	ns	3

Notes 1. $t_{WP\ (MIN.)}$ is applied to late write cycles or read modify write cycles. In early write cycles, $t_{WCH\ (MIN.)}$ should be met.

2. If $t_{WCS} \geq t_{WCS\ (MIN.)}$, the cycle is an early write cycle and the data out will remain Hi-Z through the entire cycle.

3. $t_{DS\ (MIN.)}$ and $t_{DH\ (MIN.)}$ are referenced to the $\overline{CAS}$ falling edge in early write cycles. In late write cycles and read modify write cycles, they are referenced to the $\overline{WE}$ falling edge.

Read Modify Write Cycle

Parameter	Symbol	t_{RAC} = 50 ns		t_{RAC} = 60 ns		t_{RAC} = 70 ns		t_{RAC} = 80 ns		Unit	Note
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Read modify write cycle time	t_{RWC}	133	–	158	–	180	–	200	–	ns	
$\overline{RAS}$ to $\overline{WE}$ delay time	t_{RWD}	70	–	83	–	95	–	105	–	ns	1
$\overline{CAS}$ to $\overline{WE}$ delay time	t_{CWD}	33	–	38	–	43	–	45	–	ns	1
Column address to $\overline{WE}$ delay time	t_{AWD}	45	–	53	–	60	–	65	–	ns	1

Note 1. If $t_{WCS} \geq t_{WCS\ (MIN.)}$, the cycle is an early write cycle and the data out will remain Hi-Z through the entire cycle. If $t_{RWD} \geq t_{RWD\ (MIN.)}$, $t_{CWD} \geq t_{CWD\ (MIN.)}$, $t_{AWD} \geq t_{AWD\ (MIN.)}$ and $t_{CPWD} \geq t_{CPWD\ (MIN.)}$, the cycle is a read modify write cycle and the data out will contain data read from the selected cell. If neither of the above conditions is met, the state of the data out is indeterminate.

Fast Page Mode

Parameter	Symbol	t_{RAC} = 50 ns		t_{RAC} = 60 ns		t_{RAC} = 70 ns		t_{RAC} = 80 ns		Unit	Note
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Fast page mode cycle time	t_{PC}	35	–	40	–	45	–	50	–	ns	
Access time from $\overline{CAS}$ precharge	t_{ACP}	–	30	–	35	–	40	–	45	ns	
$\overline{RAS}$ pulse width	t_{RASP}	50	125,000	60	125,000	70	125,000	80	125,000	ns	
$\overline{CAS}$ precharge time	t_{CP}	8	–	10	–	10	–	10	–	ns	
$\overline{RAS}$ hold time from $\overline{CAS}$ precharge	t_{RHCP}	30	–	35	–	40	–	45	–	ns	
Read modify write cycle time	t_{PRWC}	73	–	83	–	90	–	95	–	ns	
$\overline{CAS}$ precharge to $\overline{WE}$ delay time	t_{CPWD}	50	–	58	–	65	–	70	–	ns	1

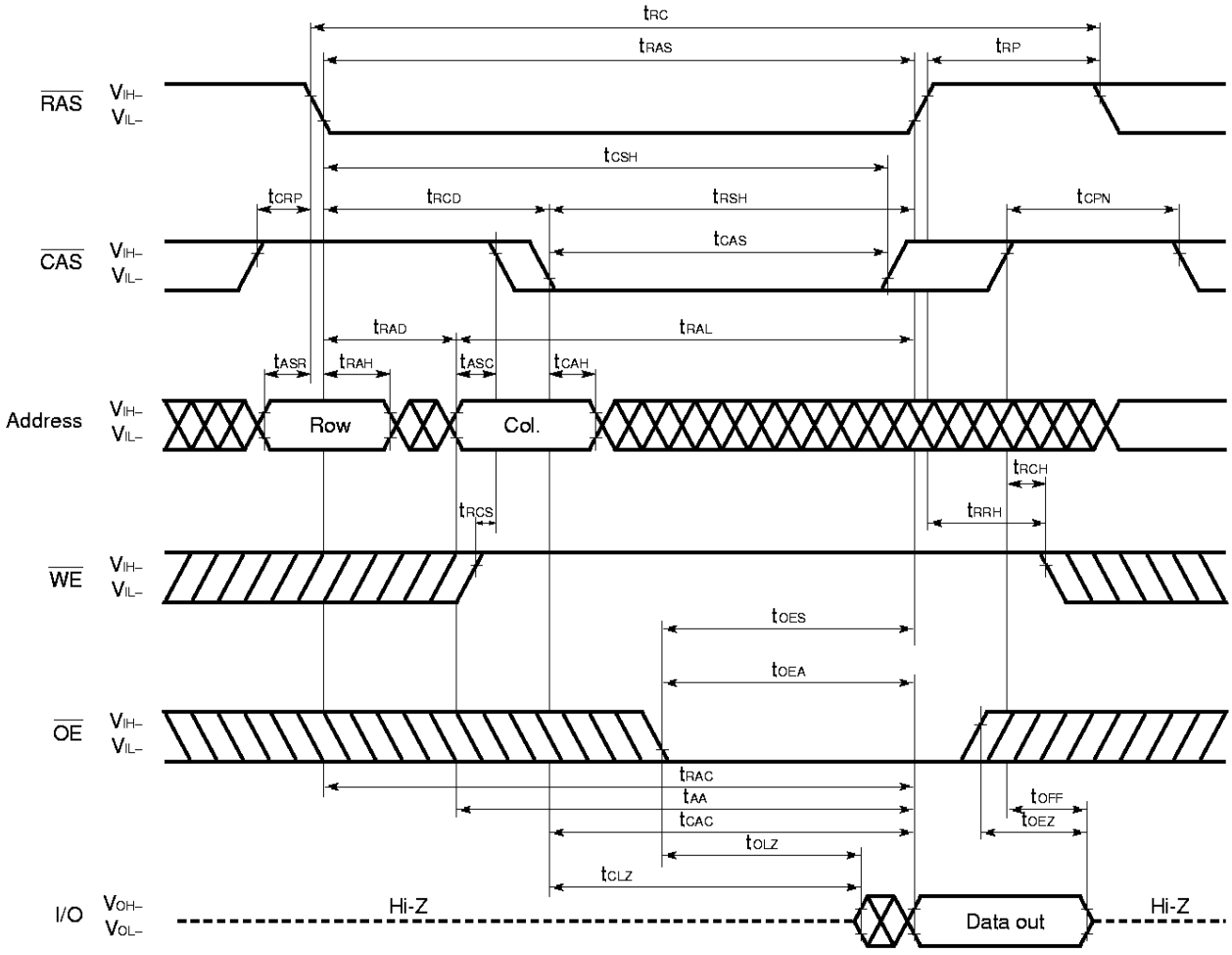
Note 1. If $t_{WCS} \geq t_{WCS\,(MIN.)}$, the cycle is an early write cycle and the data out will remain Hi-Z through the entire cycle. If $t_{RWD} \geq t_{RWD\,(MIN.)}$, $t_{CWD} \geq t_{CWD\,(MIN.)}$, $t_{AWD} \geq t_{AWD\,(MIN.)}$ and $t_{CPWD} \geq t_{CPWD\,(MIN.)}$, the cycle is a read modify write cycle and the data out will contain data read from the selected cell. If neither of the above conditions is met, the state of the data out is indeterminate.

Refresh Cycle

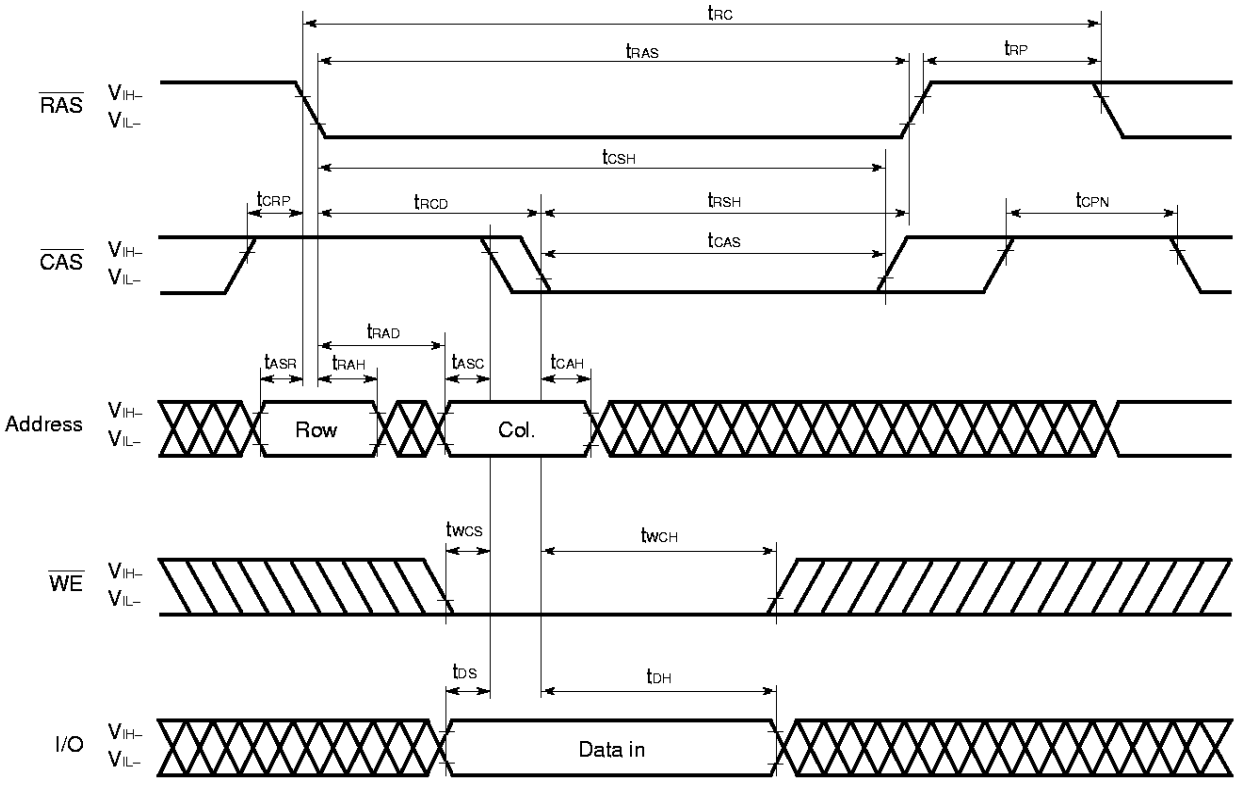
Parameter	Symbol	t_{RAC} = 50 ns		t_{RAC} = 60 ns		t_{RAC} = 70 ns		t_{RAC} = 80 ns		Unit	Note
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
$\overline{CAS}$ setup time	t_{CSR}	5	–	5	–	5	–	5	–	ns	
$\overline{CAS}$ hold time ($\overline{CAS}$ before $\overline{RAS}$ refresh)	t_{CHR}	10	–	10	–	10	–	10	–	ns	
$\overline{RAS}$ precharge $\overline{CAS}$ hold time	t_{RPC}	5	–	5	–	5	–	5	–	ns	
$\overline{RAS}$ pulse width ($\overline{CAS}$ before $\overline{RAS}$ self refresh)	t_{RASS}	100	–	100	–	100	–	100	–	μs	1
$\overline{RAS}$ precharge time ($\overline{CAS}$ before $\overline{RAS}$ self refresh)	t_{RPS}	90	–	110	–	130	–	150	–	ns	1
$\overline{CAS}$ hold time ($\overline{CAS}$ before $\overline{RAS}$ self refresh)	t_{CHS}	–50	–	–50	–	–50	–	–50	–	ns	1
$\overline{WE}$ setup time	t_{WSR}	10	–	10	–	10	–	10	–	ns	
$\overline{WE}$ hold time	t_{WHR}	15	–	15	–	15	–	15	–	ns	

Note 1. This specification is applied only to the μPD42S17800.

Read Cycle

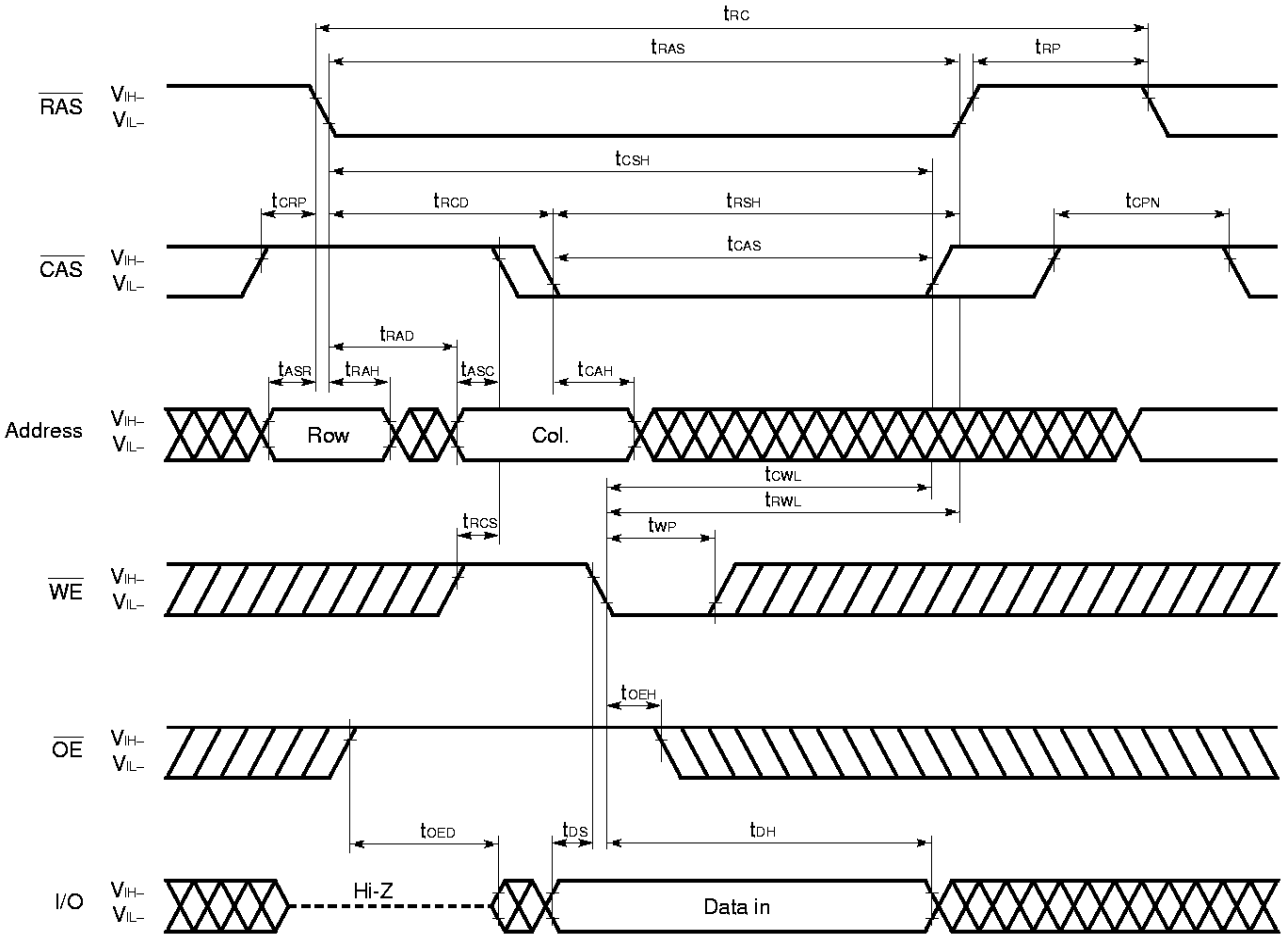

tRC
tRAS
tRP
RAS
VIH–
VIL–
tCSH
tCRP
tRCD
tRSH
tCPN
CAS
tCAS
tRAD
tRAL
tASR
tRAH
tASC
tCAH
Address
Row
Col.
tRCH
tRCS
tRRH
WE
tOES
tOEA
OE
tRAC
tAA
tOFF
tOEZ
tCAC
tOLZ
tCLZ
I/O
VOH–
VOL–
Hi-Z
Data out
Hi-Z

Early Write Cycle

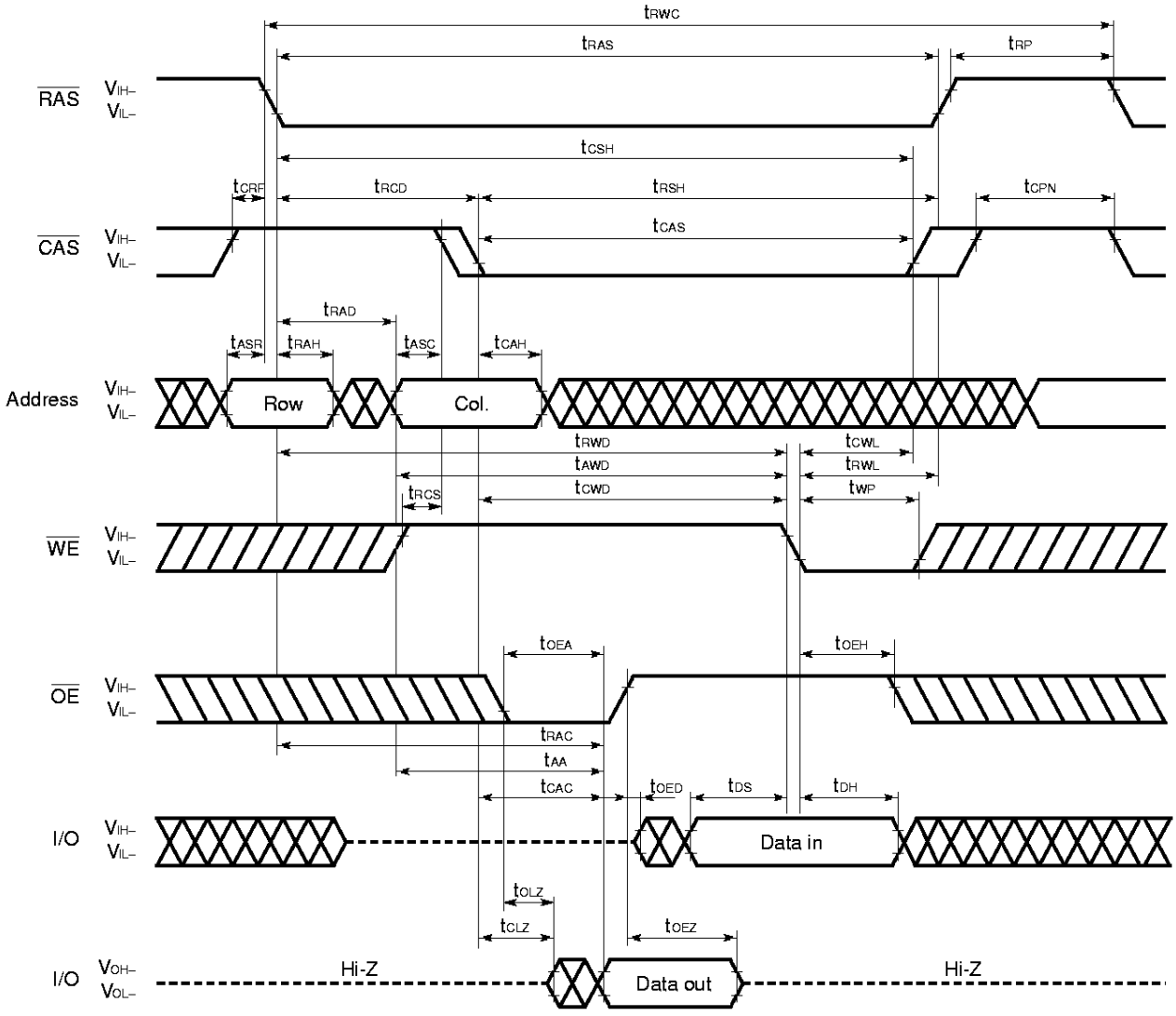


Remark $\overline{OE}$: Don't care

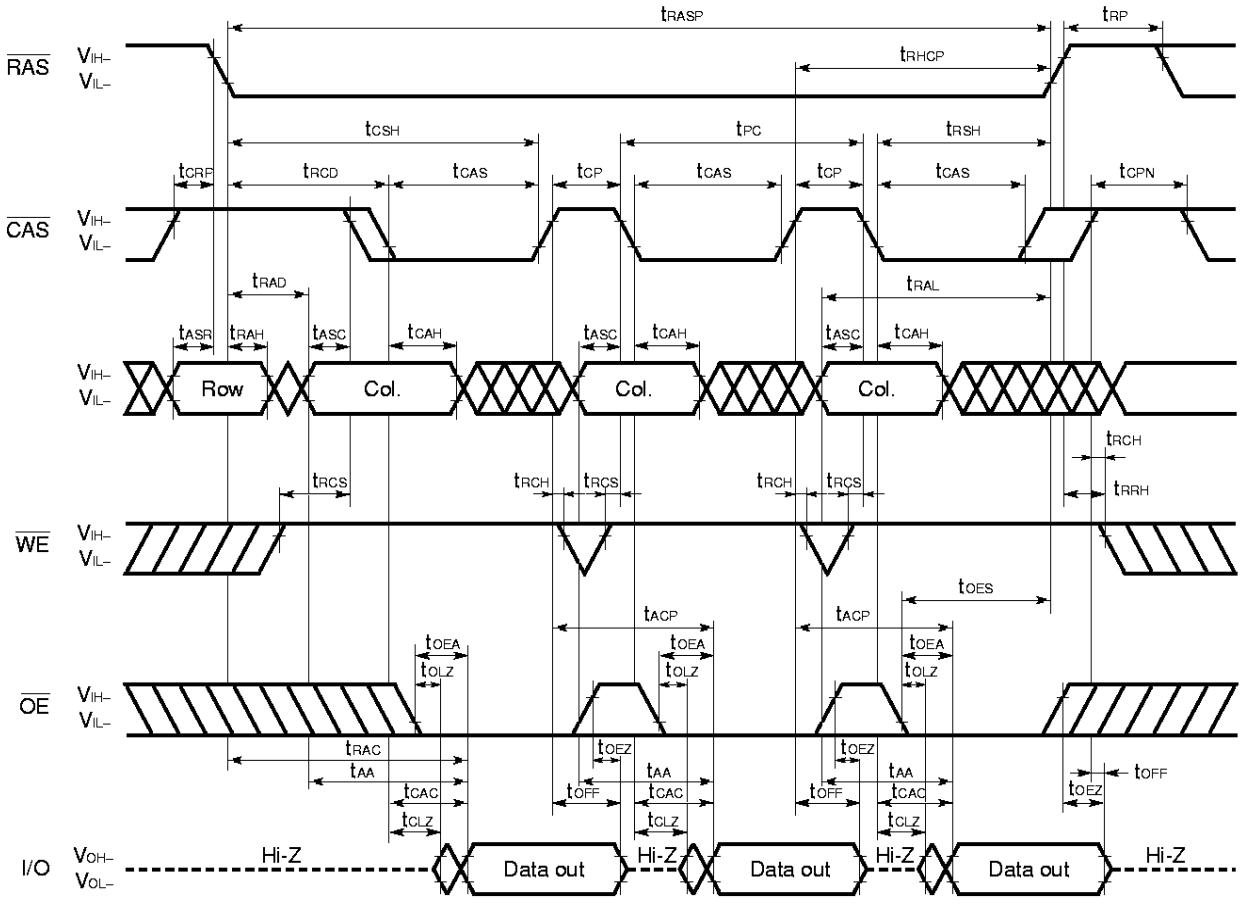
Late Write Cycle



Read Modify Write Cycle

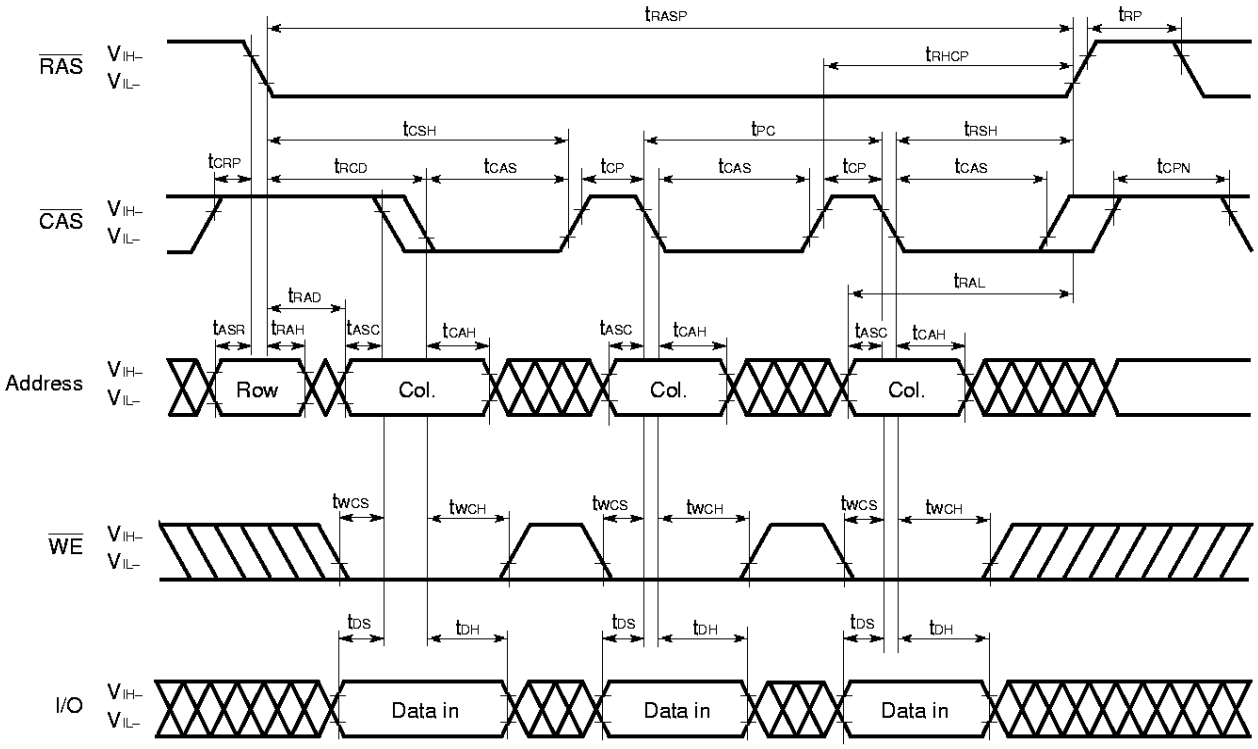


Fast Page Mode Read Cycle



Remark In the fast page mode, read, write and read modify write cycles are available for each of the consecutive $\overline{CAS}$ cycles within the same $\overline{RAS}$ cycle.

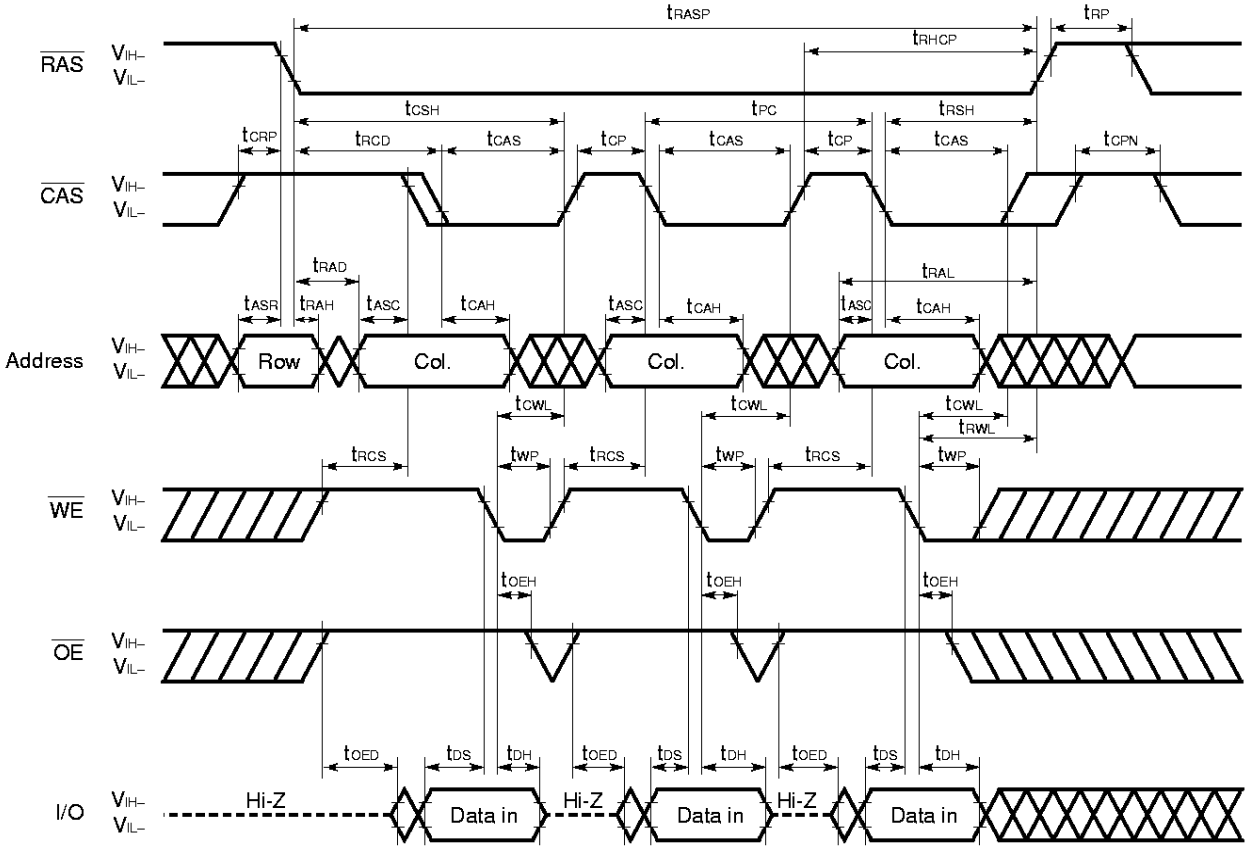
Fast Page Mode Early Write Cycle



Remarks 1. $\overline{OE}$: Don't care

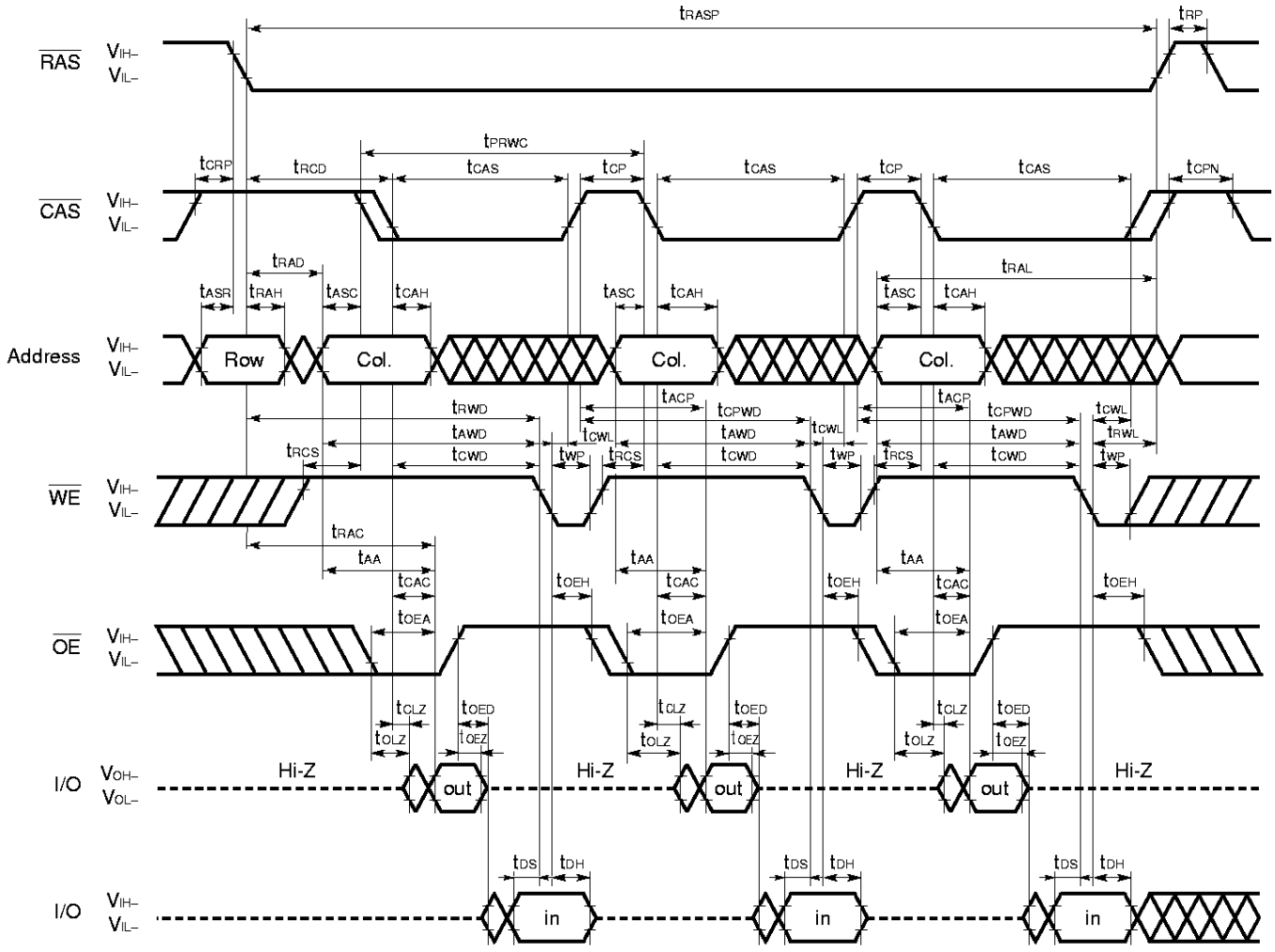
2. In the fast page mode, read, write and read modify write cycles are available for each of the consecutive $\overline{CAS}$ cycles within the same $\overline{RAS}$ cycle.

Fast Page Mode Late Write Cycle



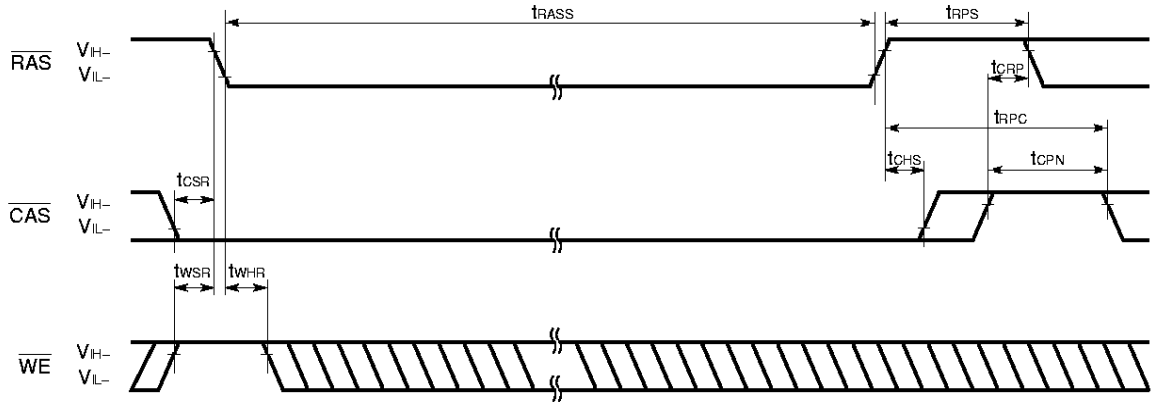
Remark In the fast page mode, read, write and read modify write cycles are available for each of the consecutive $\overline{CAS}$ cycles within the same $\overline{RAS}$ cycle.

Fast Page Mode Read Modify Write Cycle



Remark In the fast page mode, read, write and read modify write cycles are available for each of the consecutive $\overline{CAS}$ cycles within the same $\overline{RAS}$ cycle.

$\overline{CAS}$ Before $\overline{RAS}$ Self Refresh Cycle (Only for the μPD42S17800)



Remark Address, $\overline{OE}$: Don't care I/O : Hi-Z

Cautions on Use of $\overline{CAS}$ Before $\overline{RAS}$ Self Refresh

$\overline{CAS}$ before $\overline{RAS}$ self refresh can be used independently when used in combination with distributed $\overline{CAS}$ before $\overline{RAS}$ long refresh; However, when used in combination with burst $\overline{CAS}$ before $\overline{RAS}$ long refresh or with long $\overline{RAS}$ only refresh (both distributed and burst), the following cautions must be observed.

(1) Normal Combined Use of $\overline{CAS}$ Before $\overline{RAS}$ Self Refresh and Burst $\overline{CAS}$ Before $\overline{RAS}$ Long Refresh

When $\overline{CAS}$ before $\overline{RAS}$ self refresh and burst $\overline{CAS}$ before $\overline{RAS}$ long refresh are used in combination, please perform $\overline{CAS}$ before $\overline{RAS}$ refresh 2,048 times within a 32 ms interval just before and after setting $\overline{CAS}$ before $\overline{RAS}$ self refresh.

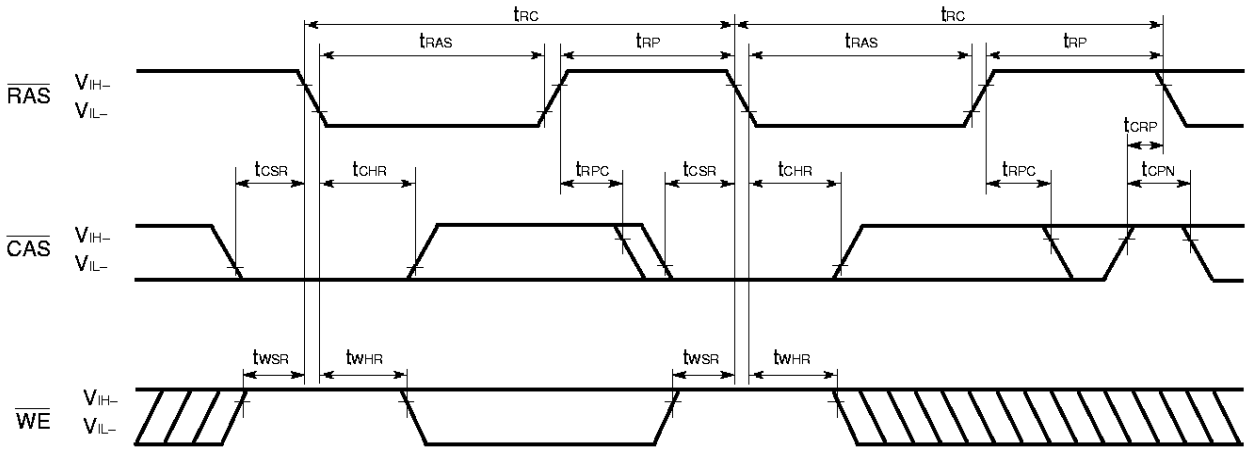
(2) Normal Combined Use of $\overline{CAS}$ Before $\overline{RAS}$ Self Refresh and Long $\overline{RAS}$ Only Refresh

When $\overline{CAS}$ before $\overline{RAS}$ self refresh and $\overline{RAS}$ only refresh are used in combination, please perform $\overline{RAS}$ only refresh 2,048 times within a 32 ms interval just before and after setting $\overline{CAS}$ before $\overline{RAS}$ self refresh.

(3) If $t_{RASS\ (MIN.)}$ is not satisfied at the beginning of $\overline{CAS}$ before $\overline{RAS}$ self refresh cycles ($t_{RAS} < 100\ \mu s$), $\overline{CAS}$ before $\overline{RAS}$ refresh cycles will be executed one time.
If $10\ \mu s < t_{RAS} < 100\ \mu s$, $\overline{RAS}$ precharge time for $\overline{CAS}$ before $\overline{RAS}$ self refresh (t_{RPS}) is applied.
And refresh cycles (2,048/128 ms) should be met.

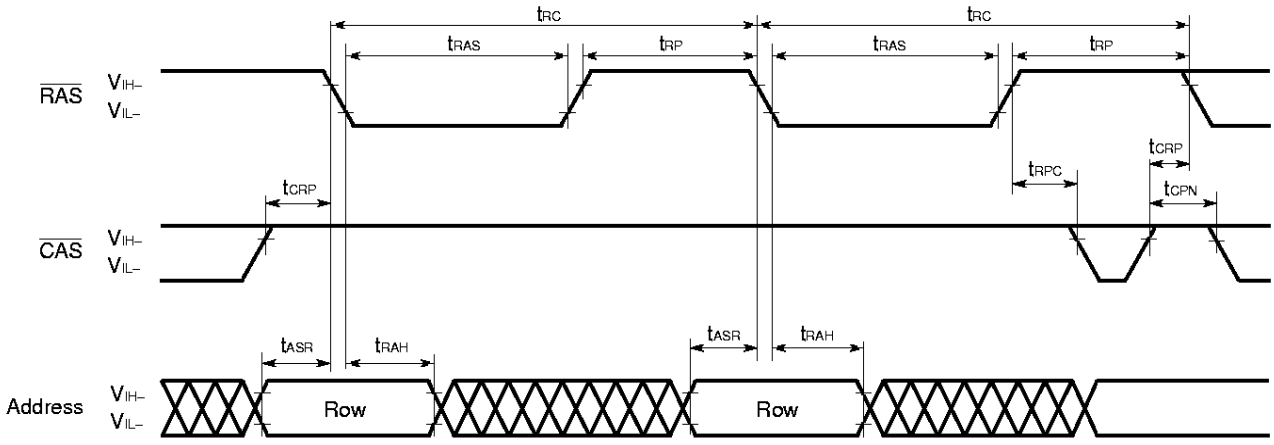
For details, please refer to **How to use DRAM** User's Manual.

$\overline{\text{CAS}}$ Before $\overline{\text{RAS}}$ Refresh Cycle



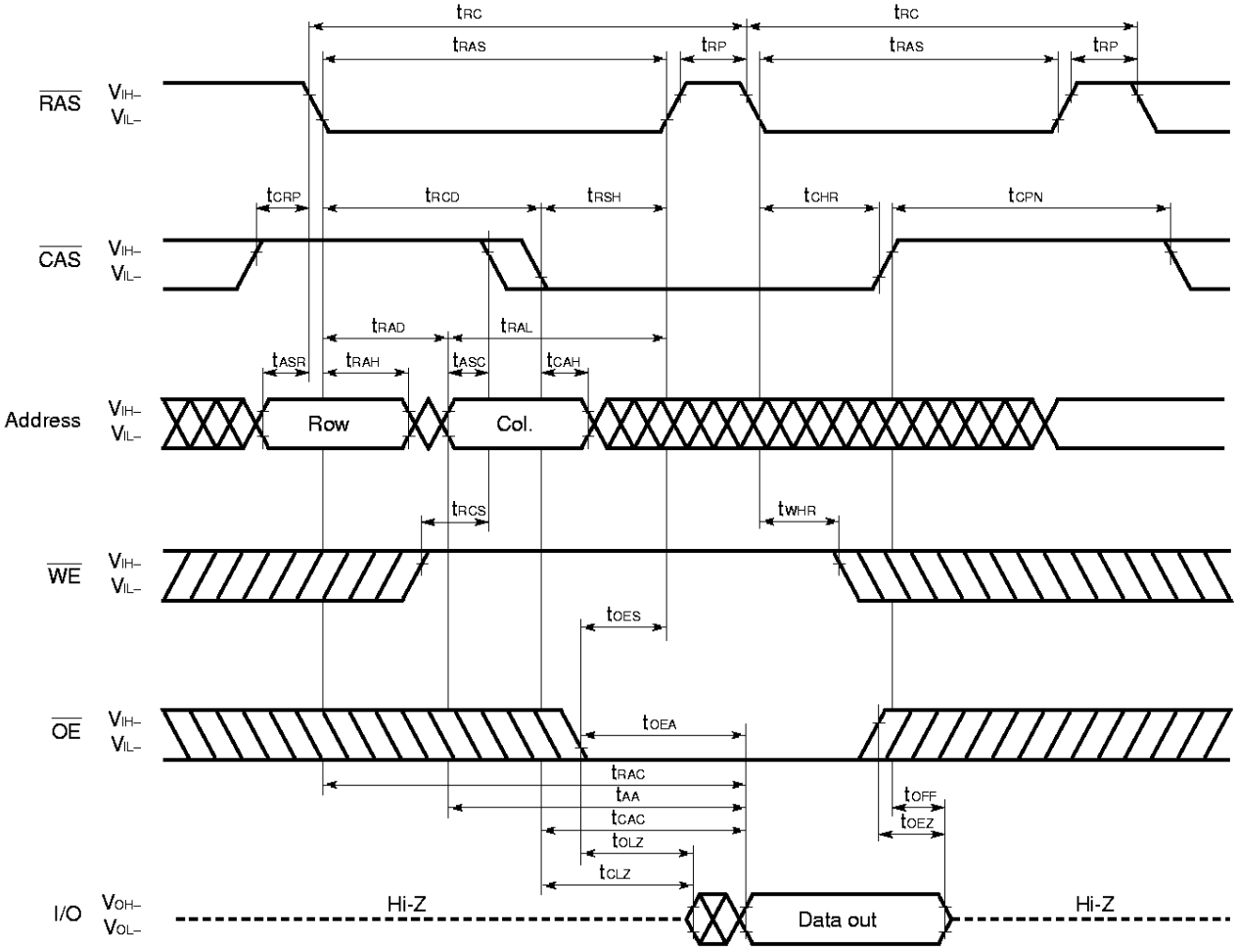
Remark Address, $\overline{\text{OE}}$: Don't care I/O: Hi-Z

$\overline{\text{RAS}}$ Only Refresh Cycle

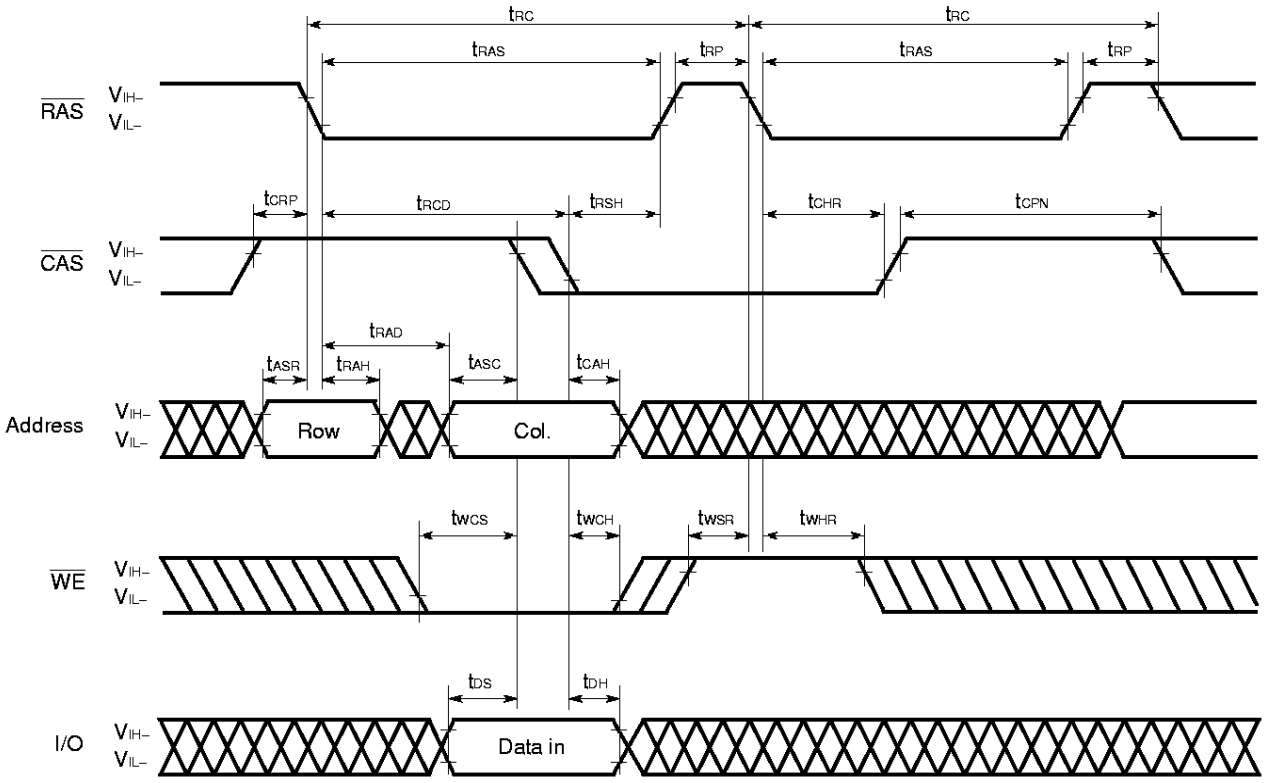


Remark $\overline{\text{WE}}$, $\overline{\text{OE}}$: Don't care I/O: Hi-Z

Hidden Refresh Cycle (Read)

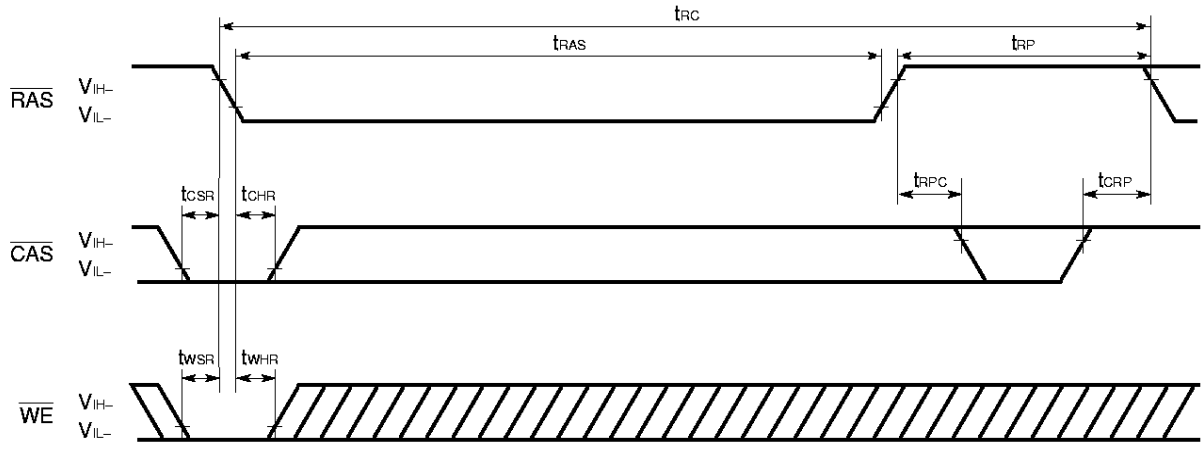


Hidden Refresh Cycle (Write)



Remark $\overline{OE}$: Don't care

Test Mode Set Cycle ($\overline{WE}$, $\overline{CAS}$ Before $\overline{RAS}$ Refresh Cycle)



Remark Address, $\overline{OE}$: Don't care I/O: Hi-Z

Test Mode

By using the test mode, the test time can be reduced. The reason for this is that, the memory emulates the × 16-bit organization during test mode. Don't care about the input level of the $\overline{CAS}$ input A0.

(1) Setting the mode

Executing the test mode cycle ($\overline{WE}$, $\overline{CAS}$ before $\overline{RAS}$ refresh cycle) sets the test mode.

(2) Write/read operation

When either a "0" or a "1" is written to the input pin in test mode, this data is written to 16 bits of memory cell.

Next, when the data is read from the output pin at the same address, the cell can be checked.

Output = "1": Normal write (all memory cells)
Output = "0": Abnormal write

(3) Refresh

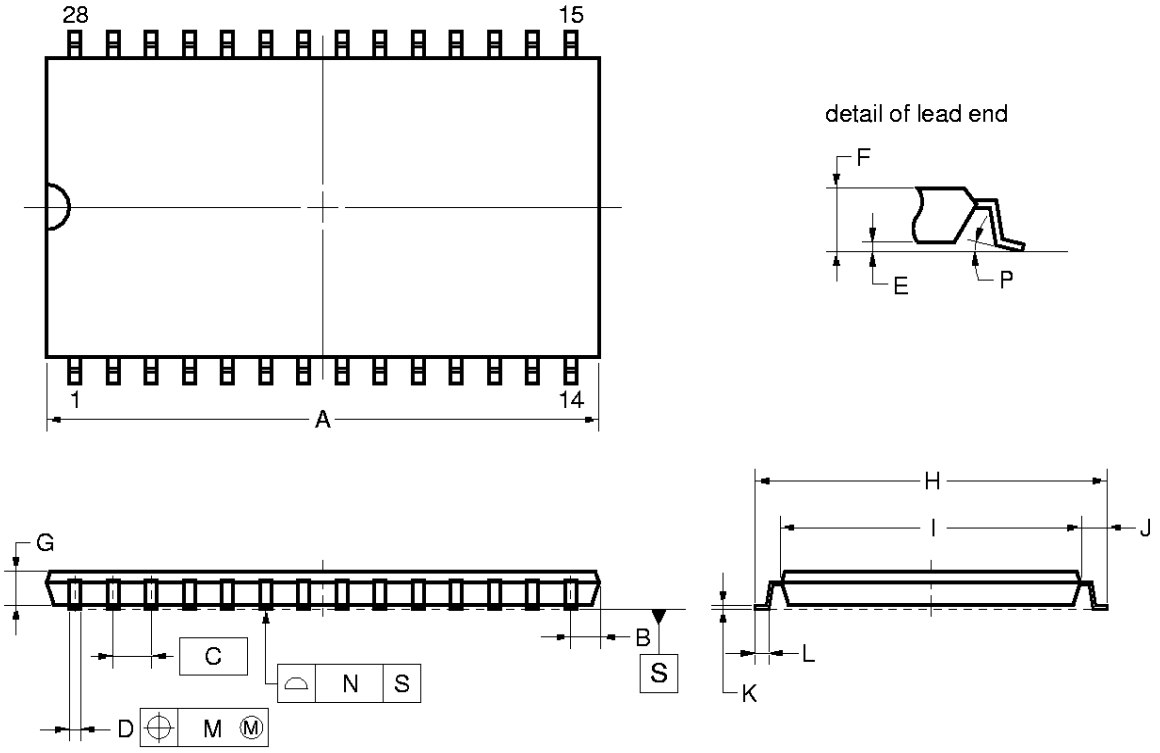
Refresh in the test mode must be performed with the $\overline{RAS}$ / $\overline{CAS}$ cycle or with the $\overline{WE}$, $\overline{CAS}$ before $\overline{RAS}$ refresh cycle. The $\overline{WE}$, $\overline{CAS}$ before $\overline{RAS}$ refresh cycle use the same counter as the $\overline{CAS}$ before $\overline{RAS}$ refresh's internal counter.

(4) Mode Cancellation

The test mode is cancelled by executing one cycle of $\overline{RAS}$ only refresh cycle or $\overline{CAS}$ before $\overline{RAS}$ refresh cycle.

Package Drawings

28PIN PLASTIC TSOP(II) (400 mil)



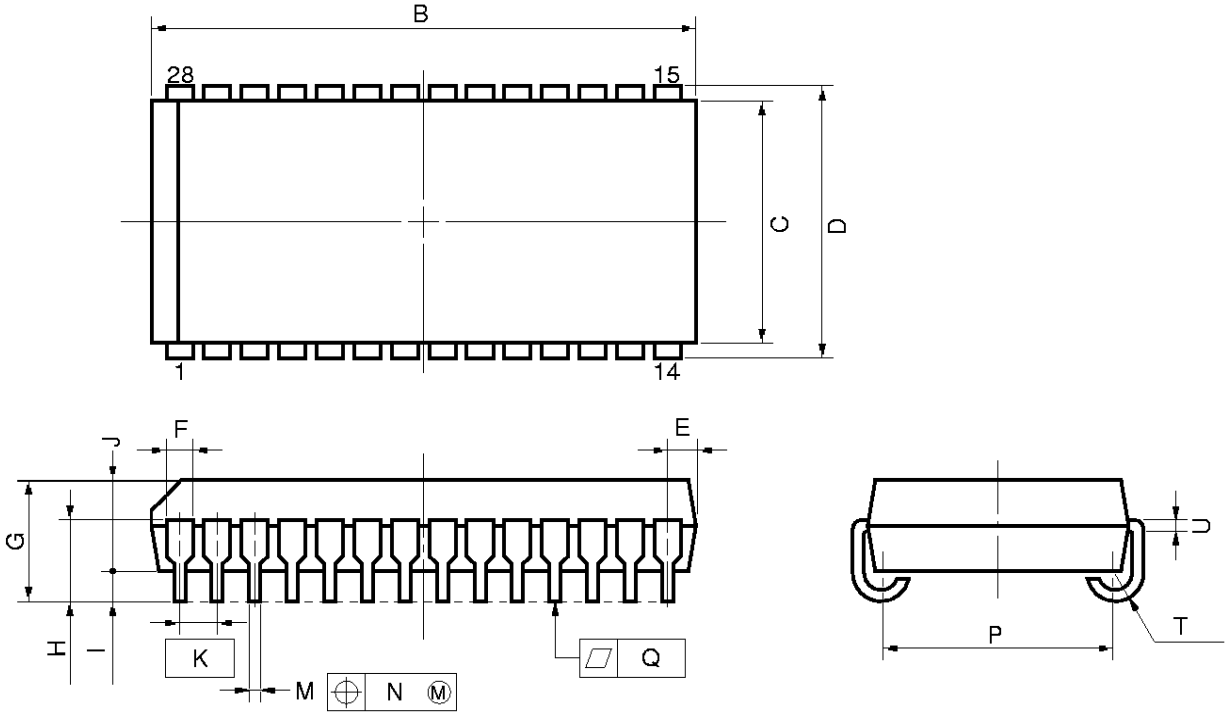
NOTE

1. Controlling dimension —— millimeter.
2. Each lead centerline is located within 0.21 mm (0.009 inch) of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS	INCHES
A	$18.37^{+0.26}_{-0.05}$	$0.723^{+0.011}_{-0.002}$
B	1.075 MAX.	0.043 MAX.
C	1.27 (T.P.)	0.050 (T.P.)
D	$0.42^{+0.08}_{-0.07}$	0.017±0.003
E	0.1±0.05	0.004±0.002
F	1.2 MAX.	0.048 MAX.
G	0.97±0.08	$0.038^{+0.004}_{-0.003}$
H	11.76±0.2	0.463±0.008
I	10.16±0.1	0.400±0.004
J	0.8±0.2	$0.031^{+0.009}_{-0.008}$
K	$0.145^{+0.025}_{-0.015}$	0.006±0.001
L	0.5±0.1	$0.020^{+0.004}_{-0.005}$
M	0.21	0.009
N	0.10	0.004
P	$3°^{+7°}_{-3°}$	$3°^{+7°}_{-3°}$

S28G5-50-7JD3-1

28 PIN PLASTIC SOJ (400 mil)



P28LE-400A1

NOTE

Each lead centerline is located within 0.12 mm (0.005 inch) of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS	INCHES
B	$18.67^{+0.2}_{-0.35}$	$0.735^{+0.008}_{-0.013}$
C	10.16	0.400
D	11.18±0.2	$0.440^{+0.008}_{-0.007}$
E	1.08±0.15	$0.043^{+0.006}_{-0.007}$
F	0.74	0.029
G	3.5±0.2	$0.138^{+0.008}_{-0.007}$
H	2.545±0.2	0.100±0.008
I	0.8 MIN.	0.031 MIN.
J	2.6	0.102
K	1.27 (T.P.)	0.050 (T.P.)
M	0.40±0.10	$0.016^{+0.004}_{-0.005}$
N	0.12	0.005
P	9.40±0.20	$0.370^{+0.008}_{-0.007}$
Q	0.10	0.004
T	R 0.85	R 0.033
U	$0.20^{+0.10}_{-0.05}$	$0.008^{+0.004}_{-0.002}$

★ Recommended Soldering Conditions

The following conditions (see tables below and next page) must be met for soldering conditions of the μPD42S17800, 4217800.

For more details, refer to our document "SEMICONDUCTOR DEVICE MOUNTING TECHNOLOGY MANUAL" (C10535E).

Please consult with our sales offices in case other soldering process is used, or in case the soldering is done under different conditions.

Types of Surface Mount Device

μPD42S17800G5-7JD, 4217800G5-7JD: 28-pin plastic TSOP (II) (400 mil)

Soldering process	Soldering conditions	Symbol
Infrared ray reflow	Peak temperature of package surface: 235 °C or lower, Reflow time: 30 seconds or less (210 °C or higher), Number of reflow processes: MAX. 3 Exposure limit: 7 days[Note] (10 hours pre-baking is required at 125 °C afterwards)	IR35-107-3
VPS	Peak temperature of package: 215 °C or lower, Reflow time: 40 seconds or less (200 °C or higher), Number of reflow processes: MAX. 3 Exposure limit: 7 days[Note] (10 hours pre-baking is required at 125 °C afterwards)	VP15-107-3
Partial heating method	Terminal temperature: 300 °C or lower, Time: 3 seconds or lower (Per side of the package).	———

Note Exposure limit before soldering after dry-pack package is opened.
Storage conditions: 25 °C and relative humidity at 65 % or less.

Caution Do not apply more than one soldering method at any one time, except for "Partial heating method".

μPD42S17800LE, 4217800LE: 28-pin plastic SOJ (400 mil)

Soldering process	Soldering conditions	Symbol
Infrared ray reflow	Peak temperature of package surface: 235 °C or lower, Reflow time: 30 seconds or less (210 °C or higher), Number of reflow processes: MAX. 3 Exposure limit: 7 days[Note] (20 hours pre-baking is required at 125 °C afterwards)	IR35-207-3
VPS	Peak temperature of package: 215 °C or lower, Reflow time: 40 seconds or less (200 °C or higher), Number of reflow processes: MAX. 3 Exposure limit: 7 days[Note] (20 hours pre-baking is required at 125 °C afterwards)	VP15-207-3
Partial heating method	Terminal temperature: 300 °C or lower, Time: 3 seconds or less (Per side of the package).	———

Note Exposure limit before soldering after dry-pack package is opened.
Storage conditions: 25 °C and relative humidity at 65 % or less.

Caution Do not apply more than one soldering method at any one time, except for "Partial heating method".

[MEMO]

NOTES FOR CMOS DEVICES

① PRECAUTION AGAINST ESD FOR SEMICONDUCTORS

Note: Strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred. Environmental control must be adequate. When it is dry, humidifier should be used. It is recommended to avoid using insulators that easily build static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work bench and floor should be grounded. The operator should be grounded using wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with semiconductor devices on it.

② HANDLING OF UNUSED INPUT PINS FOR CMOS

Note: No connection for CMOS device inputs can be cause of malfunction. If no connection is provided to the input pins, it is possible that an internal input level may be generated due to noise, etc., hence causing malfunction. CMOS device behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using a pull-up or pull-down circuitry. Each unused pin should be connected to V_{DD} or GND with a resistor, if it is considered to have a possibility of being an output pin. All handling related to the unused pins must be judged device by device and related specifications governing the devices.

③ STATUS BEFORE INITIALIZATION OF MOS DEVICES

Note: Power-on does not necessarily define initial status of MOS device. Production process of MOS does not define the initial operation status of the device. Immediately after the power source is turned ON, the devices with reset function have not yet been initialized. Hence, power-on does not guarantee out-pin levels, I/O settings or contents of registers. Device is not initialized until the reset signal is received. Reset operation must be executed immediately after power-on for devices having reset function.

M4 96.5